



UD4606

Power MOSFET

DUAL ENHANCEMENT MODE (N-CHANNEL/P-CHANNEL)

DESCRIPTION

The UTC **UD4606** provides excellent $R_{DS(ON)}$ and low gate charge by using advanced trench technology MOSFETs. The complementary MOSFETs may help to form a level shifted high side switch and also for lots of other applications.

FEATURES

* N-Channel: 30V/6.9A

$R_{DS(ON)} = 22.5\text{ m}\Omega$ (typ.) @ $V_{GS} = 10\text{V}$

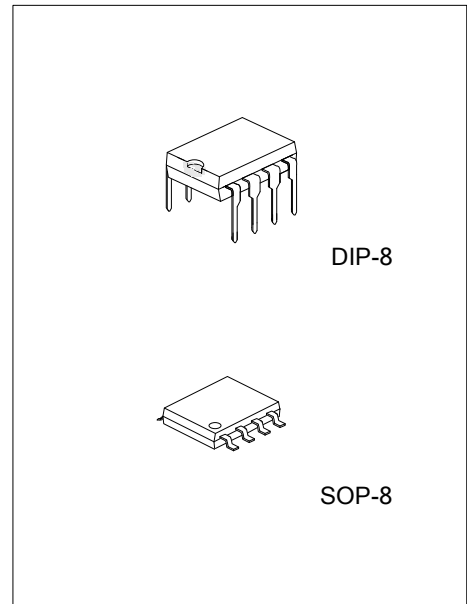
$R_{DS(ON)} = 34.5\text{ m}\Omega$ (typ.) @ $V_{GS} = 4.5\text{V}$

* P-Channel: -30V/-6A

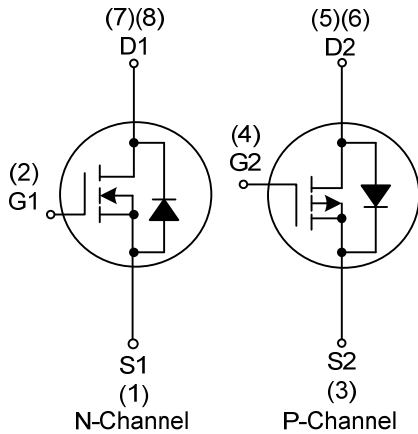
$R_{DS(ON)} = 28\text{ m}\Omega$ (typ.) @ $V_{GS} = -10\text{V}$

$R_{DS(ON)} = 44\text{ m}\Omega$ (typ.) @ $V_{GS} = -4.5\text{V}$

* Reliable and rugged



SYMBOL

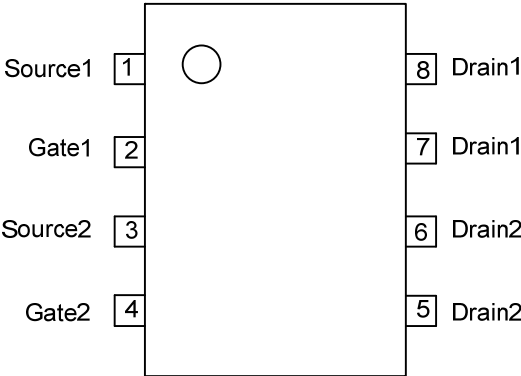


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free Plating	Halogen Free		1	2	3	4	5	6	7	8	
UD4606L-D08-T	UD4606G-D08-T	DIP-8	S1	G1	S2	G2	D2	D2	D1	D1	Tube
UD4606L-S08-R	UD4606G-S08-R	SOP-8	S1	G1	S2	G2	D2	D2	D1	D1	Tape Reel

UD4606L-D08-T	(1)Packing Type	(1) R: Tape Reel, T: Tube
	(2)Package Type	(2) D08: DIP-8, S08: SOP-8
	(3)Lead Plating	(3) G: Halogen Free, L: Lead Free

■ PIN CONFIGURATION



■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

N-CHANNEL

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note2)	I_D	6.9	A
Pulsed Drain Current (Note2)	I_{DM}	30	A
Power Dissipation	DIP-8	2.5	W
	SOP-8	2	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

P-CHANNEL

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 2)	I_D	-6	A
Pulsed Drain Current (Note 2)	I_{DM}	-30	A
Power Dissipation	DIP-8	2.5	W
	SOP-8	2	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (Note)	DIP-8		74	110	$^\circ\text{C/W}$
	SOP-8		67	80	$^\circ\text{C/W}$

Note: Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$

■ ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

N-CHANNEL

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=24\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.9	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=6.9\text{A}$		22.5	28	m Ω
		$V_{GS}=4.5\text{V}, I_D=5\text{A}$		34.5	42	m Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1.0\text{MHz}$		680		pF
Output Capacitance	C_{OSS}			102		pF
Reverse Transfer Capacitance	C_{RSS}			77		pF
SWITCHING CHARACTERISTICS						
Turn-ON Delay Time (Note2)	$t_{D(ON)}$	$V_{DS}=15\text{V}, V_{GS}=10\text{V}, R_G=3\Omega, R_L=2.2\Omega$		4.6		ns
Turn-ON Rise Time	t_R			4.1		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			20.6		ns
Turn-OFF Fall Time	t_F			5.2		ns

■ ELECTRICAL CHARACTERISTICS(Cont.)

N-CHANNEL

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Total Gate Charge (Note2)	Q_G	$V_{DS}=15V, V_{GS}=10V, I_D=6.9A$		13.8		nC
Gate-Source Charge	Q_{GS}			1.82		nC
Gate-Drain Charge	Q_{GD}			3.2		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	$I_S=1A, V_{GS}=0V$		0.76	1	V
Diode Continuous Forward Current (Note3)	I_S				3	A
Reverse Recovery Time	t_{RR}	$I_{DS}=6.9A, dl/dt=100A/\mu s$		16.5		ns
Reverse Recovery Charge	Q_{RR}			7.8		nC

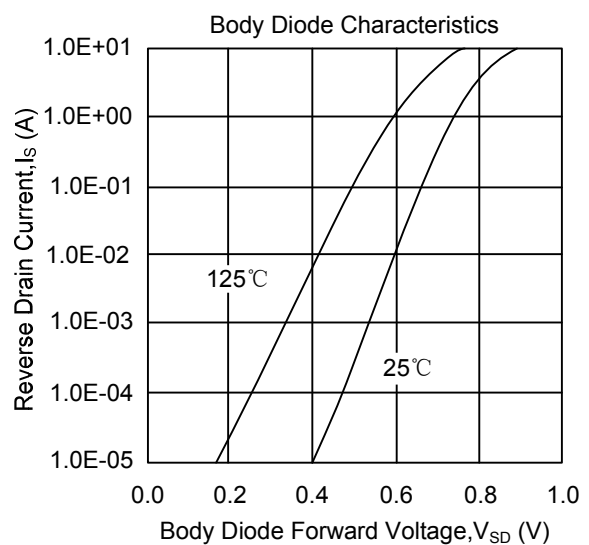
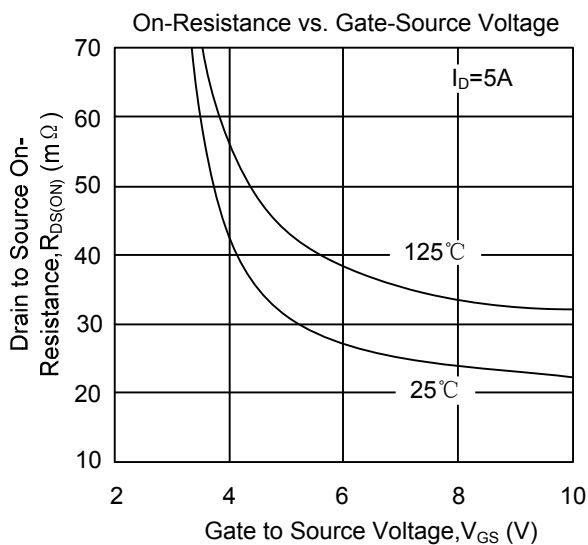
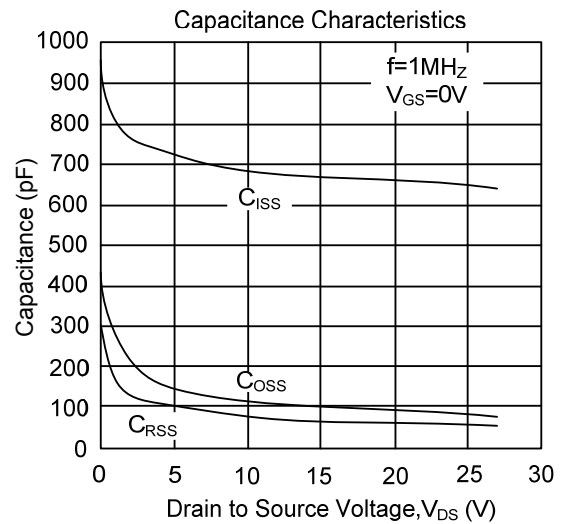
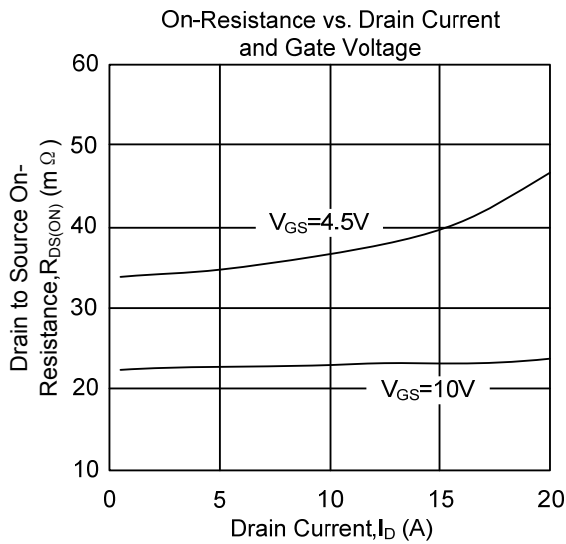
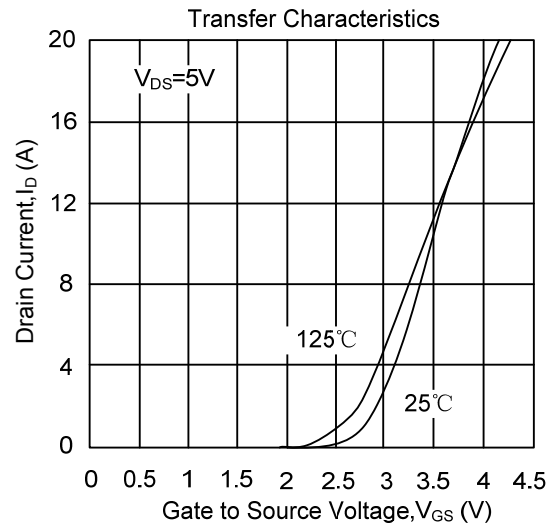
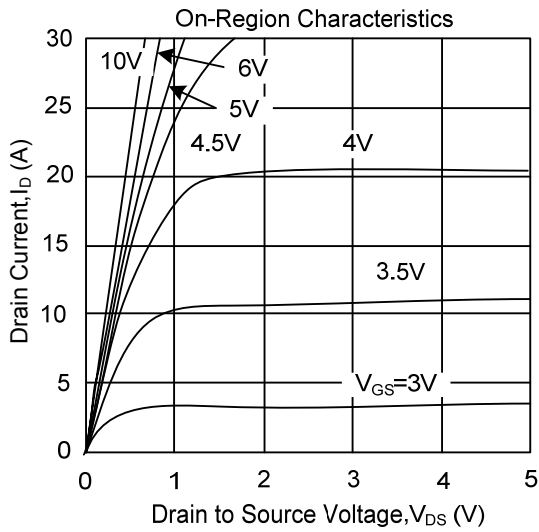
P-CHANNEL

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.2	-2	-2.4	V
Drain-Source On-State Resistance (Note2)	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-6A$		28	35	m Ω
		$V_{GS}=-4.5V, I_D=-5A$		44	58	m Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=-15V, f=1.0MHz$		920		pF
Output Capacitance	C_{OSS}			190		pF
Reverse Transfer Capacitance	C_{RSS}			122		pF
SWITCHING CHARACTERISTICS						
Turn-ON Delay Time (Note2)	$t_{D(ON)}$	$V_{DS}=-15V, V_{GS}=-10V,$ $R_G=3\Omega, R_L=2.7\Omega$		7.7		ns
Turn-ON Rise Time	t_R			5.7		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			20.2		ns
Turn-OFF Fall Time	t_F			9.5		ns
Total Gate Charge (Note2)	Q_G	$V_{DS}=-15V, V_{GS}=-10V, I_D=-6A$		18.5		nC
Gate-Source Charge	Q_{GS}			2.7		nC
Gate-Drain Charge	Q_{GD}			4.5		nC
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	$I_S=-1A, V_{GS}=0V$		-0.76	-1	V
Diode Continuous Forward Current (Note3)	I_S				-4.2	A
Reverse Recovery Time	t_{RR}	$I_{DS}=-6A, dl/dt=100A/\mu s$		20		ns
Reverse Recovery Charge	Q_{RR}			8.8		nC

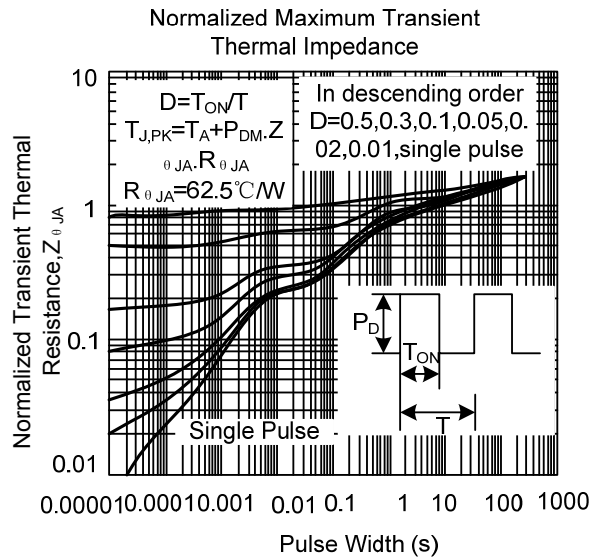
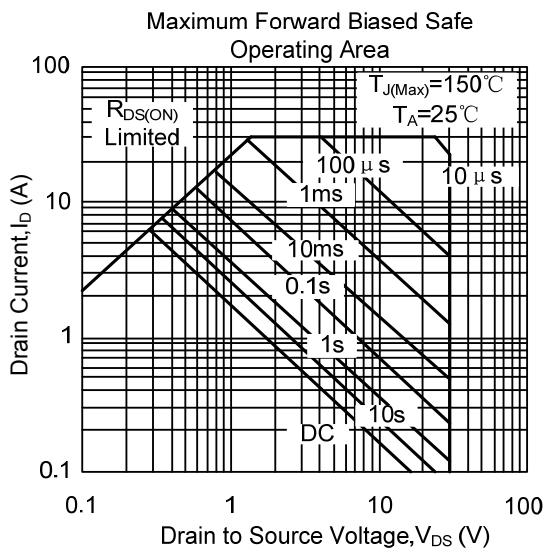
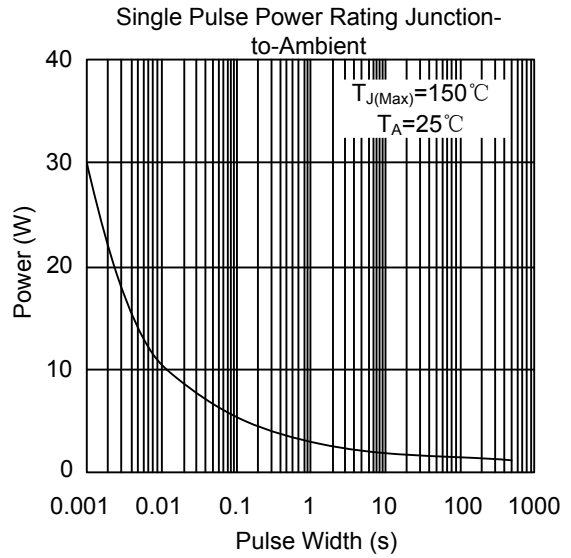
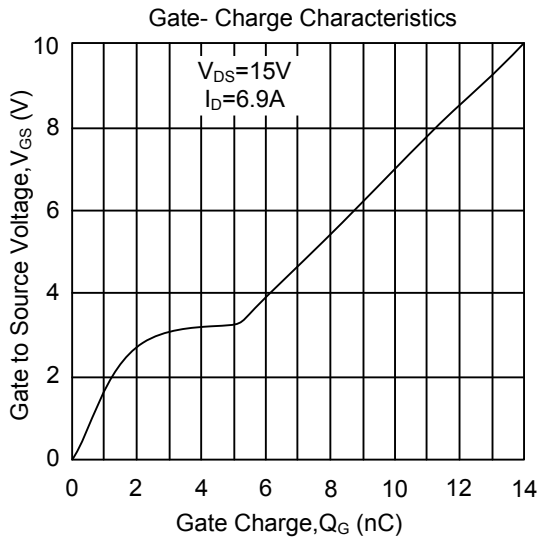
- Notes: 1. Pulse width limited by $T_{J(MAX)}$
 2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 3. Surface Mounted on $1in^2$ pad area, $t \leq 10sec$.

TYPICAL CHARACTERISTICS

N-CHANNEL

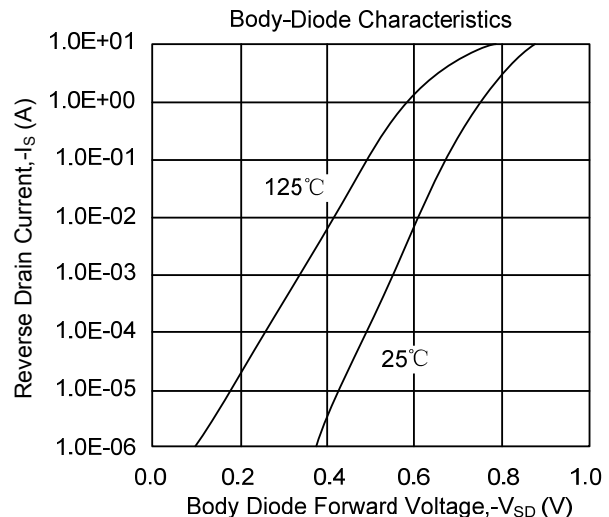
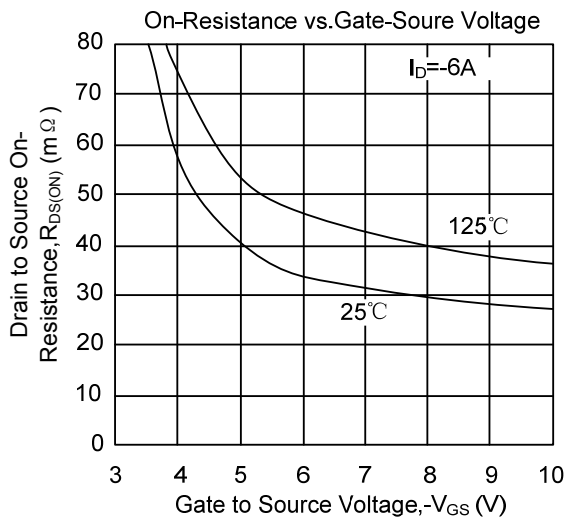
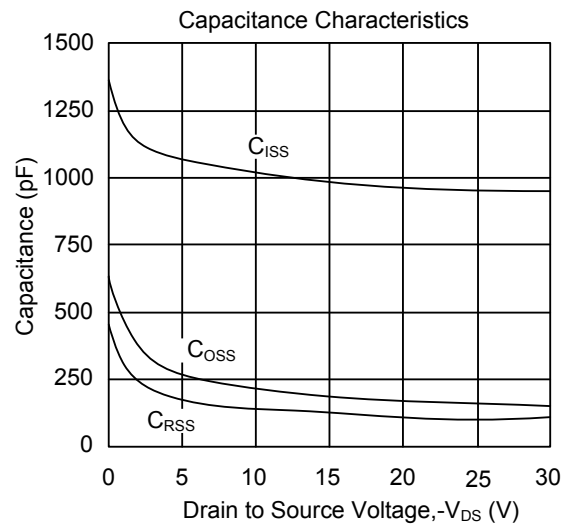
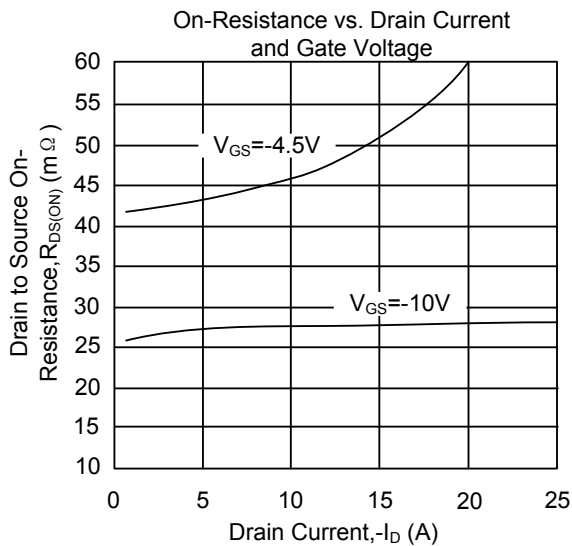
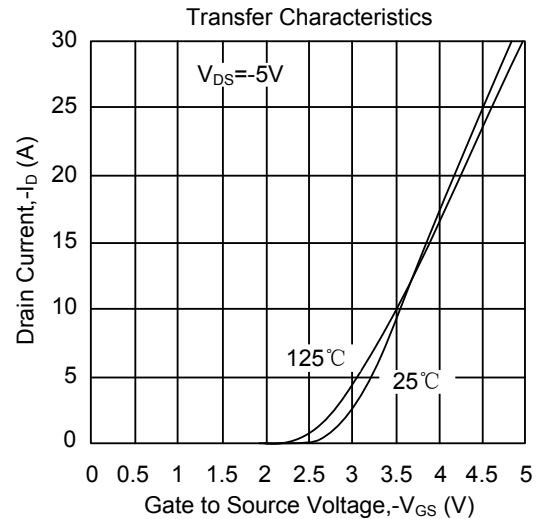
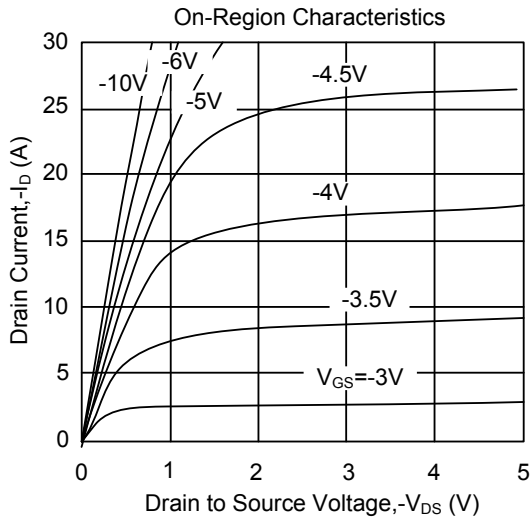


■ TYPICAL CHARACTERISTICS(Cont.)

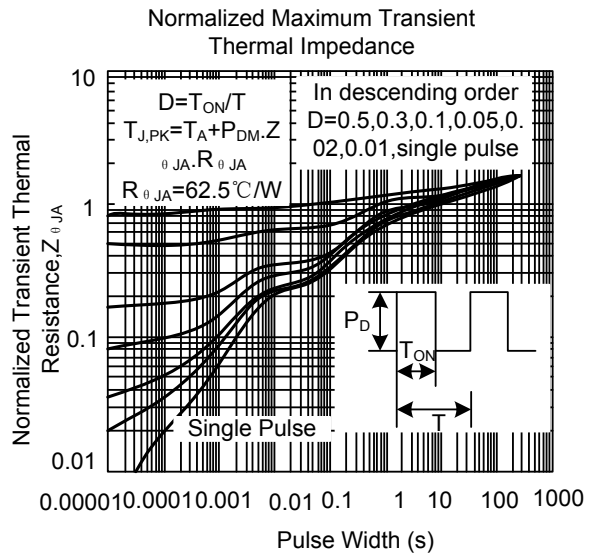
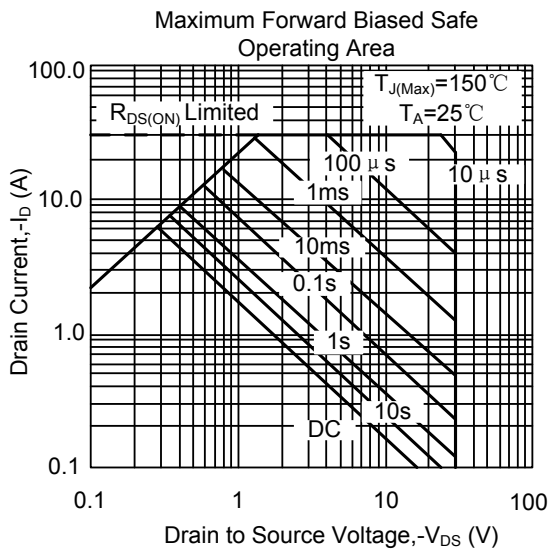
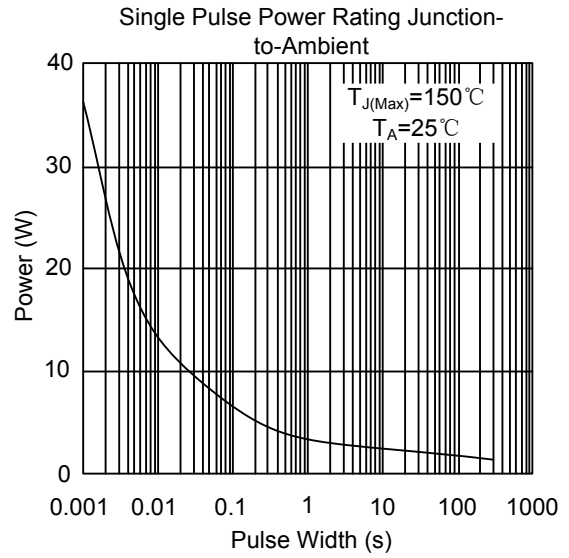
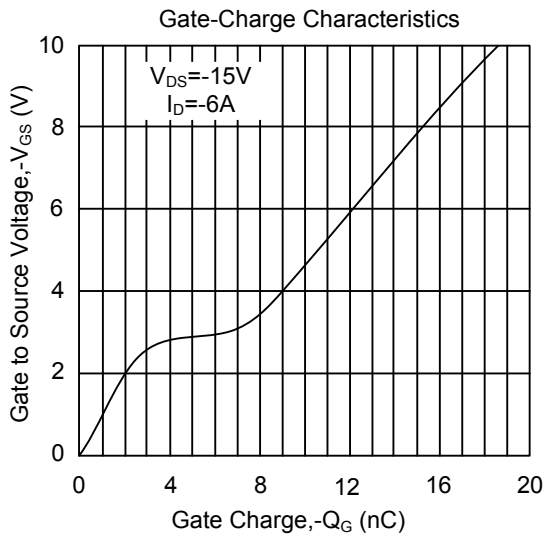


■ TYPICAL CHARACTERISTICS(Cont.)

P-CHANNEL

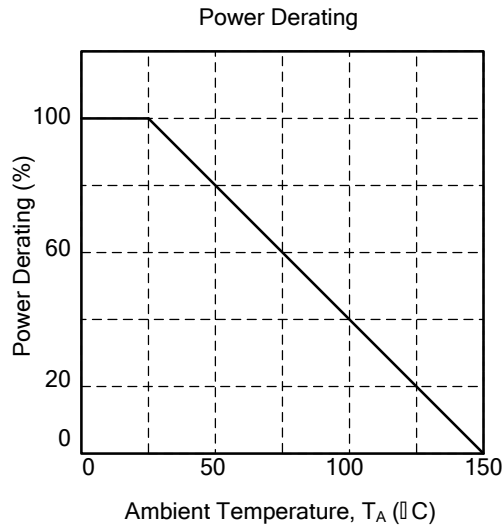


TYPICAL CHARACTERISTICS(Cont.)



■ TYPICAL CHARACTERISTICS(Cont.)

For N / P-CHANNEL



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